AOD4C60/AOI4C60

600V,4A N-Channel MOSFET

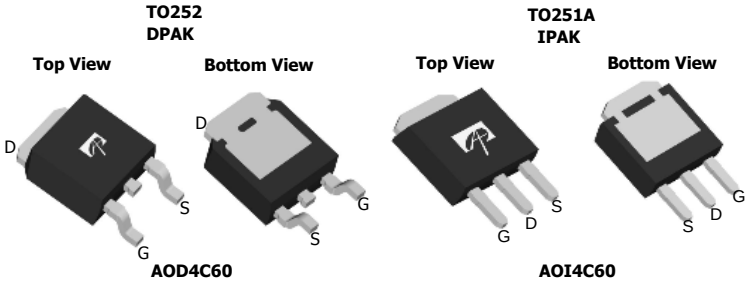
General Description

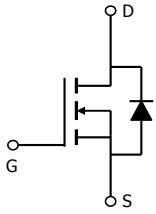
The AOD4C60 & AOI4C60 are fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications. By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

Product Summary

V_{DS} @ $T_{j,max}$	700V
I_{DM}	27A
$R_{DS(ON),max}$	< 0.95Ω
$Q_{g,typ}$	14nC
E_{oss} @ 400V	2.7µJ

100% UIS Tested!
100% R_g Tested!





Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current[B]	T_C=25℃	I_D	4	A
	T_C=100℃		3.5	
Pulsed Drain Current [C]		I_{DM}	27	
Avalanche Current [C,K]		I_{AR}	4	A
Repetitive avalanche energy [C,K]		E_{AR}	8	mJ
Single pulsed avalanche energy [H]		E_{AS}	326	mJ
MOSFET dv/dt ruggedness		dv/dt	100	V/ns
Peak diode recovery dv/dt			20	
Power Dissipation [B]	T_C=25℃	P_D	125	W
	Derate above 25°C		1	W/ °C
Junction and Storage Temperature Range		T_J, T_{STG}	-50 to 150	℃
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	℃

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient [A,G]	$R_{\theta JA}$	45	55	℃/W
Maximum Case-to-sink [A]	$R_{\theta CS}$	-	0.5	℃/W
Maximum Junction-to-Case [D,F]	$R_{\theta JC}$	0.7	1	℃/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V, T_J=25°C	600			V
		I_D=250µA, V_{GS}=0V, T_J=150°C		700		
BV_{DSS} /ΔTJ	Zero Gate Voltage Drain Current	ID=250µA, VGS=0V		0.57		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=600V, V_{GS}=0V			1	µA
		V_{DS}=480V, T_J=125°C			10	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±30V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V, I_D=250µA	3	4	5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=1.3A		0.78	0.95	Ω
g_{FS}	Forward Transconductance	V_{DS}=40V, I_D=2A		4		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.74	1	V
I_S	Maximum Body-Diode Continuous Current				4	A
I_{SM}	Maximum Body-Diode Pulsed Current [C]				27	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz		910		pF
C_{oss}	Output Capacitance			41		pF
$C_{o(er)}$	Effective output capacitance, energy related [I]	V_{GS}=0V, V_{DS}=0 to 480V, f=1MHz		32		pF
$C_{o(tr)}$	Effective output capacitance, time related [J]			55		pF
C_{rss}	Reverse Transfer Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz		1.8		pF
R_g	Gate resistance	f=1MHz		4.2		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=480V, I_D=4A		14	18	nC
Q_{gs}	Gate Source Charge			5.5		nC
Q_{gd}	Gate Drain Charge			2.9		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=300V, I_D=4A, R_G=25Ω		24		ns
t_r	Turn-On Rise Time			21		ns
$t_{D(off)}$	Turn-Off DelayTime			39		ns
t_f	Turn-Off Fall Time			19		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=4A,dI/dt=100A/µs,V_{DS}=100V		295		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=4A,dI/dt=100A/µs,V_{DS}=100V		3.6		µC

A. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A=25°C.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C in a TO252 package, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C.

G.These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

H. L=60mH, I_{AS}=3.3A, V_{DD}=150V, R_G=10Ω, Starting T_J=25°C.

I. $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

J. $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

K. L=1.0mH, V_{DD}=150V, R_G=25Ω, Starting T_J=25°C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

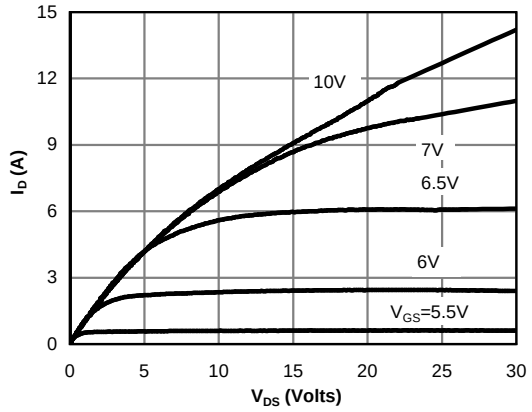


Fig 1: On-Region Characteristics

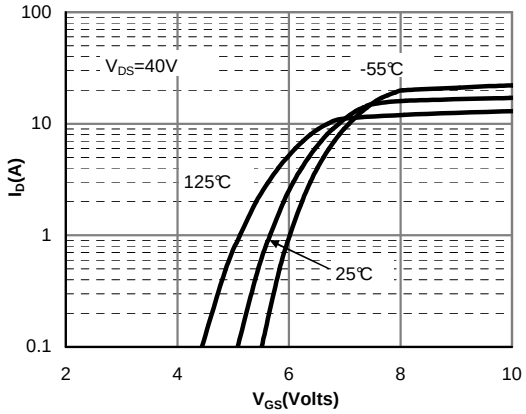


Figure 2: Transfer Characteristics

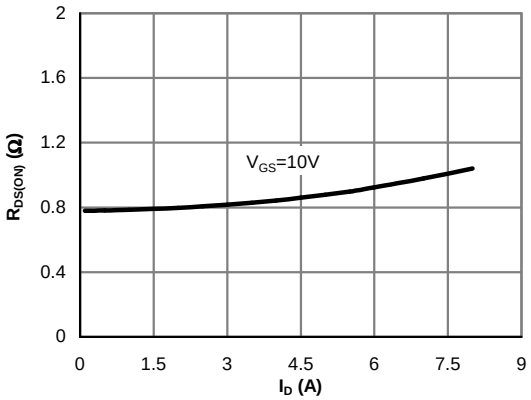


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

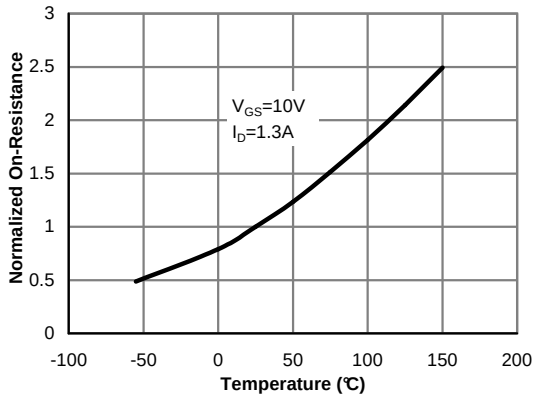


Figure 4: On-Resistance vs. Junction Temperature

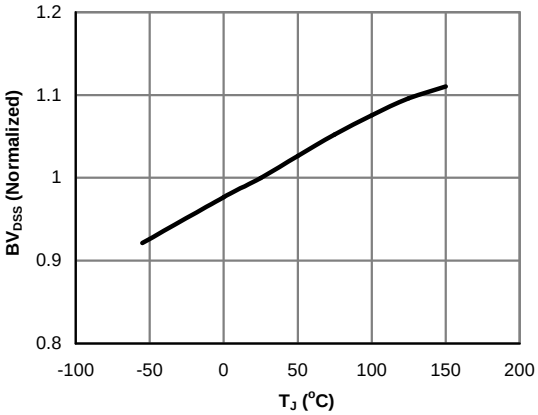


Figure 5: Break Down vs. Junction Temperature

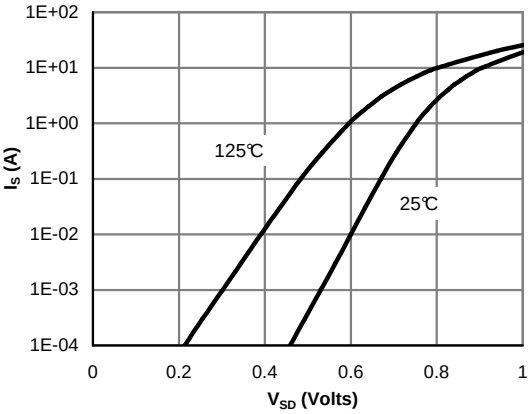


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

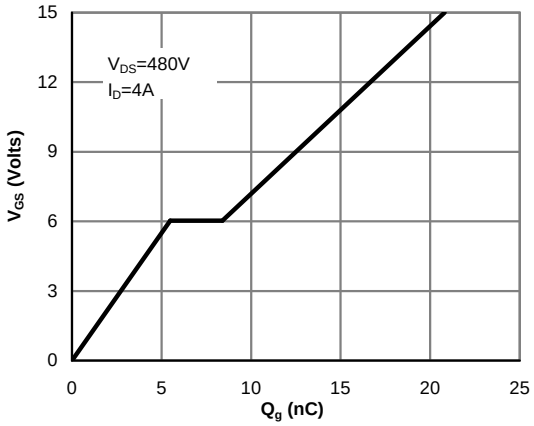


Figure 7: Gate-Charge Characteristics

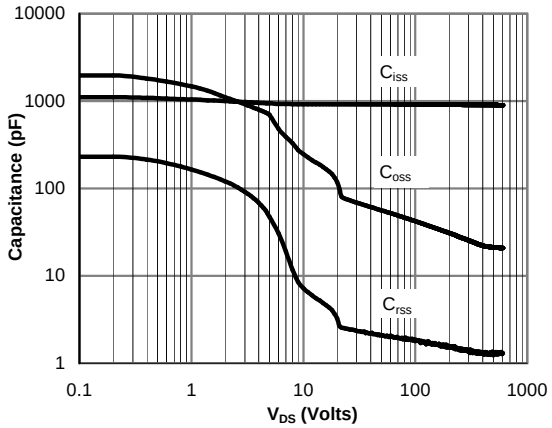


Figure 8: Capacitance Characteristics

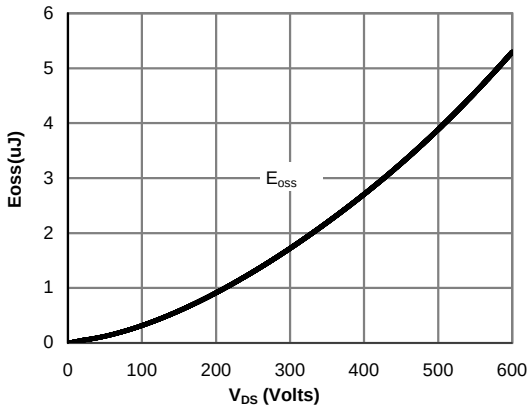


Figure 9: Coss stored Energy

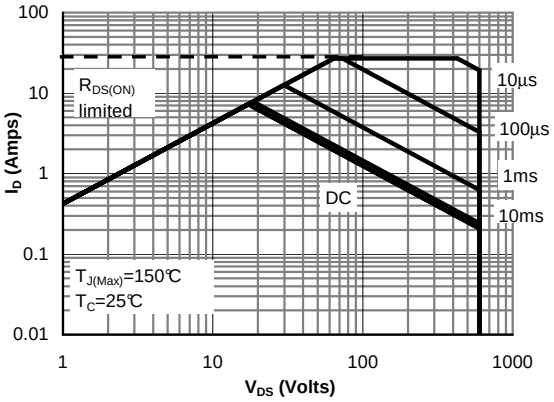


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

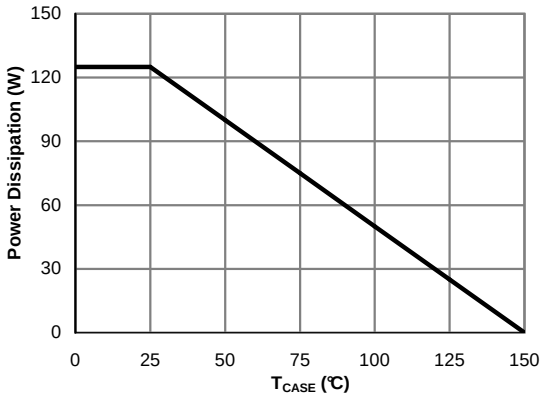


Figure 11: Power De-rating (Note B)

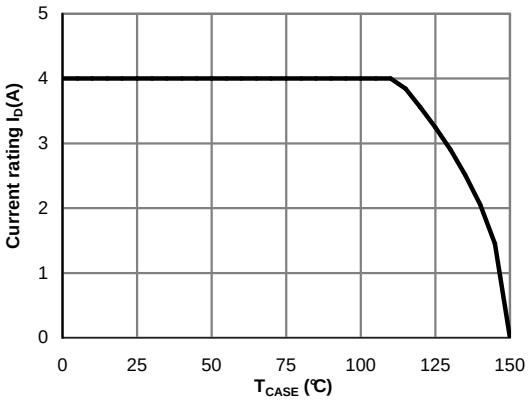


Figure 12: Current De-rating (Note B)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

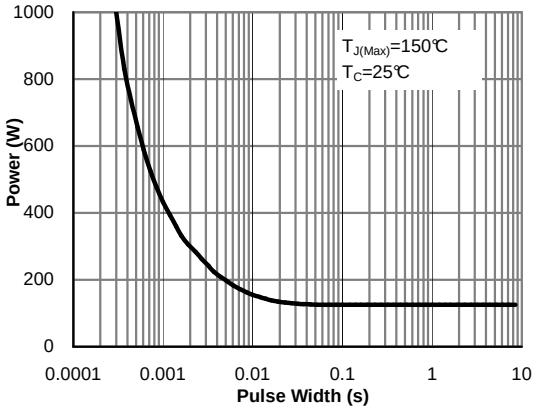


Figure 13: Single Pulse Power Rating Junction-to-Case (Note F)

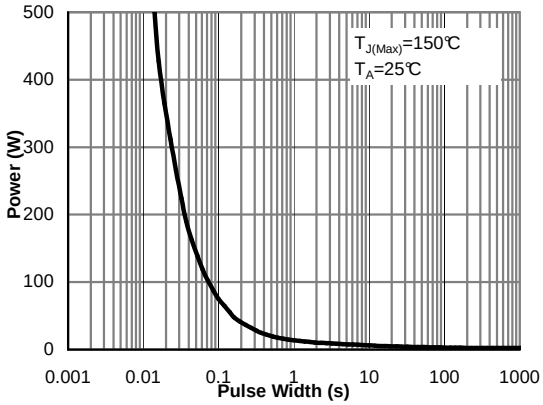


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

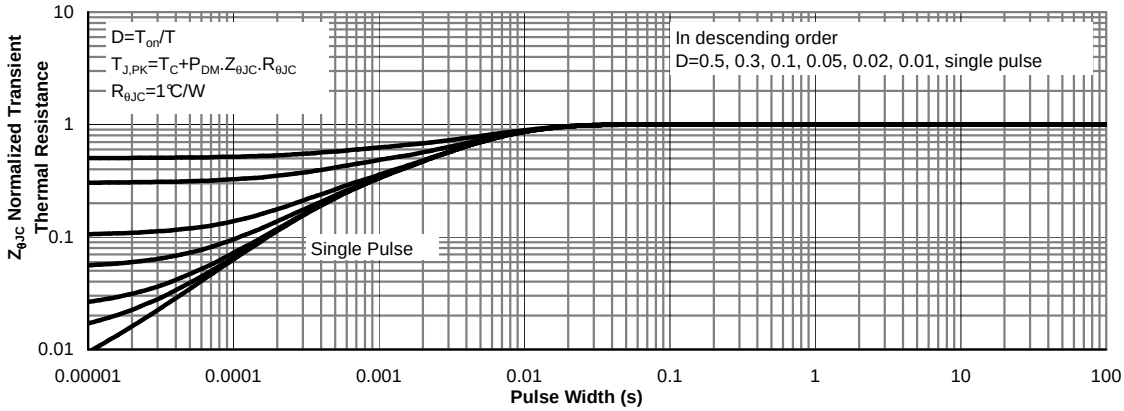


Figure 15: Normalized Maximum Transient Thermal Impedance (Note F)

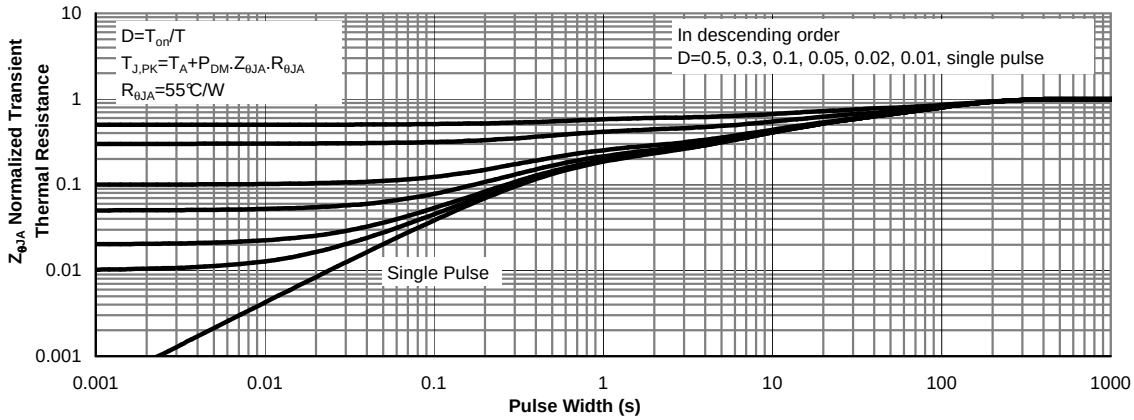
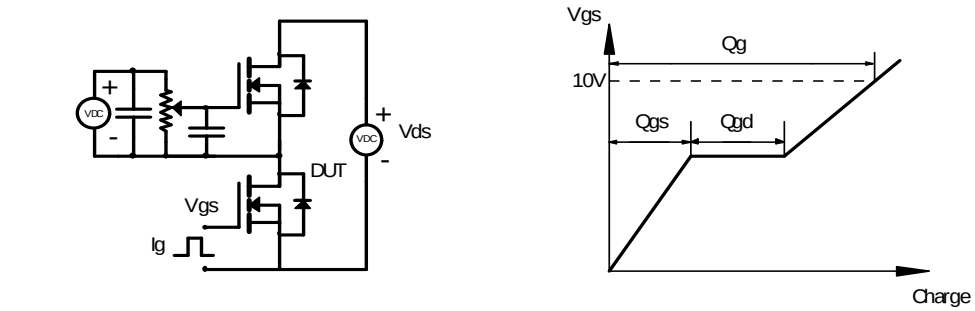
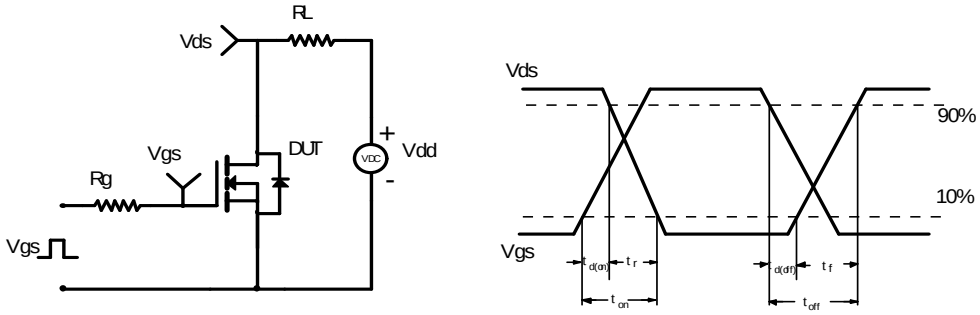


Figure 16: Normalized Maximum Transient Thermal Impedance (Note G)

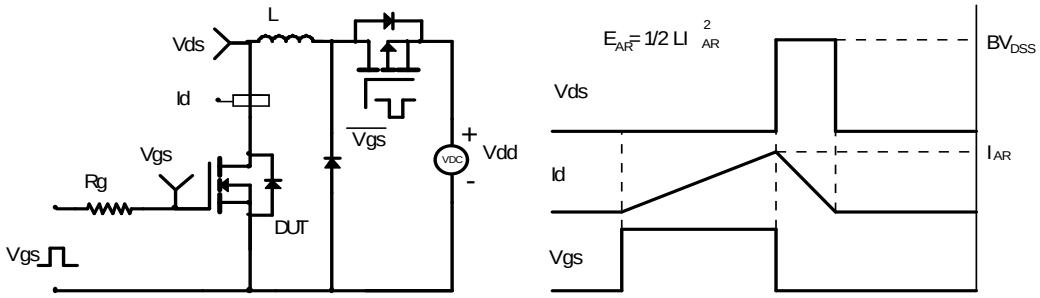
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms